

**Notice of References Cited**Application No.  
**09/241,695**Applicant(s)  
**Miyanaga et al.**Examiner  
**Shouxiang Hu**Group Art Unit  
**2811**

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A	5,893,740	4/13/99	Chang et al.	438	289
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U	Son et al., "Comparative Study of Several Anti-Punchthrough Designs for Buried Channel PMOSFET, " Device Reserach Conference Digest	6/97
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